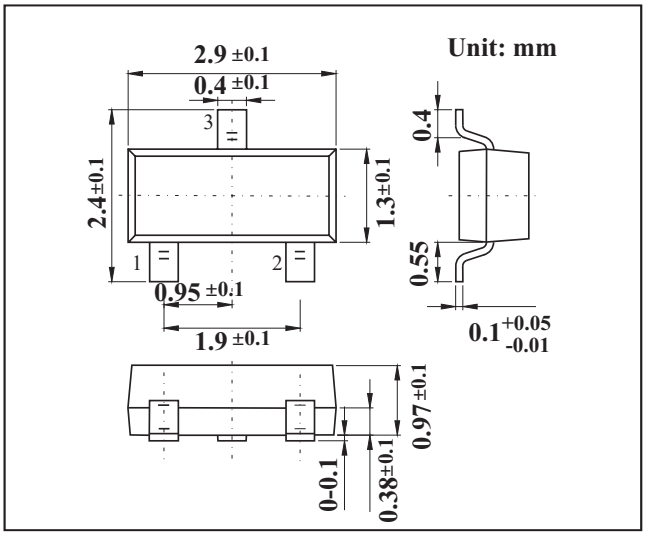
SOT-23 Plastic-Encapsulate Diodes

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

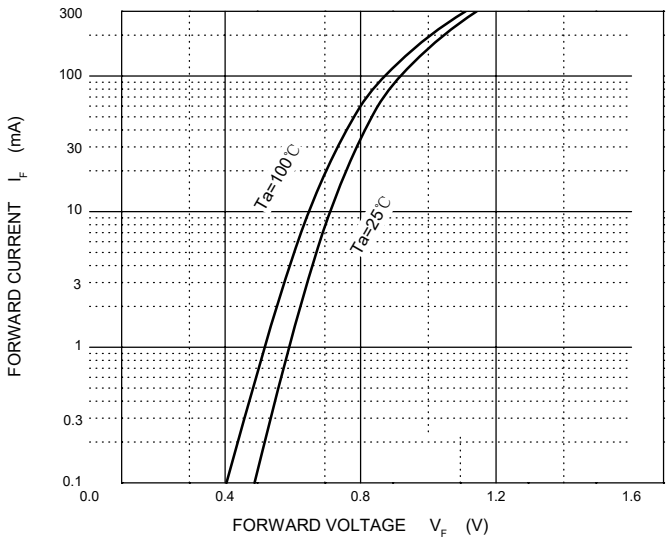
Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	℃/W
Thermal Resistance Junction to Case	$R_{\theta JC}$	26	℃/W
Operation Junction and Storage Temperature Range	T_J,T_{STG}	-55~+150	℃

Electrical Specification (T_A=25°C unless otherwise specified)

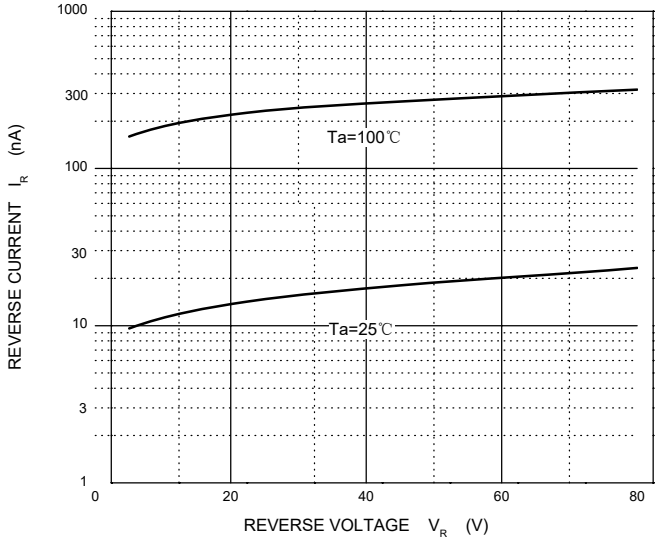
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	70			V	I_R=100μA
Forward voltage	V_{F1}			0.715	V	I_F=1mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1	V	I_F=50mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_R	2.5			μA	V_R=70V
Capacitance between terminals	C_T			1.5	pF	V_R=0,f=1MHz
Reverse recovery time	t_{rr}			6	ns	I_F = I_R = 10mA, Irr= 0.1 x I_R, R_L = 100Ω

RATINGS AND CHARACTERISTIC CURVES

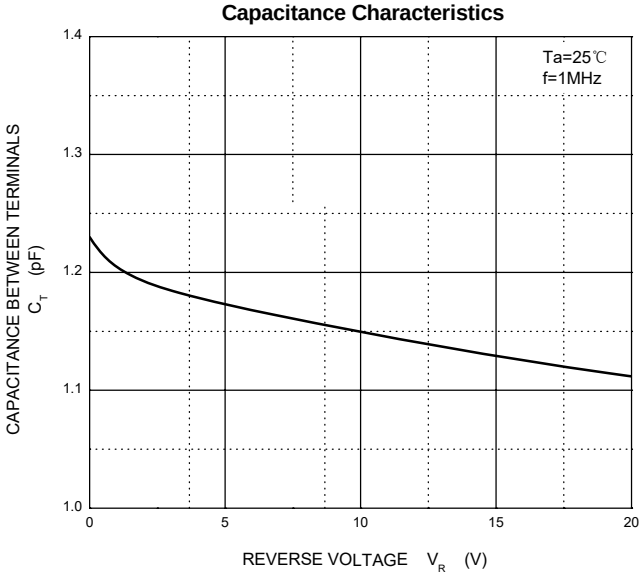
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve